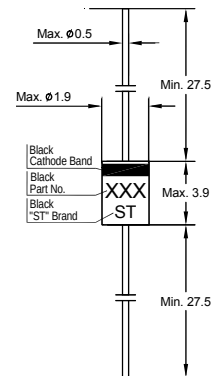


SILICON EPITAXIAL PLANAR DIODE

High Voltage Switching Diode

Features

- High reverse voltage ($V_R = 250\text{ V}$)
- High reliability with glass seal



Glass Case DO-35
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25\text{ °C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	300	V
Reverse Voltage	V_R	250	V
Average Forward Current	$I_{F(AV)}$	200	mA
Peak Forward Current	I_{FM}	625	mA
Non-Repetitive Peak Forward Surge Current (at $t = 1\text{ s}$)	I_{FSM}	1	A
Power Dissipation	P_{tot}	400	mW
Junction Temperature	T_j	175	°C
Storage Temperature Range	T_{stg}	- 65 to + 175	°C

Electrical Characteristics at $T_a = 25\text{ °C}$

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at $I_F = 100\text{ mA}$	V_F	-	1	V
Reverse Current at $V_R = 250\text{ V}$ at $V_R = 300\text{ V}$	I_R	- -	0.2 100	μA
Total Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_T	1.5	-	pF
Reverse Recovery Time at $I_F = I_R = 30\text{ mA}$, $I_{rr} = 3\text{ mA}$, $R_L = 100\text{ }\Omega$	t_{rr}	-	100	ns

